

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	467	(chip die) with (porous near1 structure layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 13:39
L2	192	(chip die) with (porous near1 structure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 14:01
L3	57	(chip die) near3 (porous near1 structure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 13:40
L4	0	2 with (insulat%3 near layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 13:50
L5	24	2 and (semiconductor wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 13:50
L6	0	("2004/0112633").URPN.	USPAT	OR	ON	2006/02/22 13:59
L7	25	(chip die) with (porous near1 structure) with (dielectric insulating insulation resin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 14:03
L8	4	7 and (wafer silicon semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 14:03

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L9	881	(chip die) with porous with (dielectric insulating insulation resin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 16:06
L10	264	9 and (wafer silicon semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 14:03
L11	258	10 not 3 not 7 not 8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 14:15
L12	258	11 and porous	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 14:15
L13	58	12 and (porous near1 structure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 14:57
L14	1	"5841193".pn. and (capacitor inductor passive resistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 14:58
L15	1	"5841193".pn. and "220"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:36
L16	13994	(chip die) with (substrate board carrer) with (passive capacitor resistor inductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:37

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L17	4232	(chip die) near4 (substrate board carrer) near4 (passive capacitor resistor inductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:38
L18	2637	(chip die) near3 (substrate board carrer) near3 (passive capacitor resistor inductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:54
L19	0	18 and @ad<"2001"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:39
L20	1418	18 and @ay<"2001"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:55
L21	194	die near3 (substrate board carrer) near3 (passive capacitor resistor inductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:54
L22	85	21 and @ay<"2001"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 16:47

## EAST Search History

L23	32	("4410905"   "4439813"   "4680613"   "4879631"   "4984059"   "4994936"   "5010387"   "5063432"   "5095402"   "5099306"   "5103283"   "5140496"   "5155656"   "5200364"   "5212402"   "5228192"   "5266821"   "5272590"   "5283717"   "5304506"   "5307309"   "5329237"   "5369545"   "5403784"   "5444600"   "5498906"   "5633785"   "5767564"   "5786230"   "5841182"   "5880925"   "5982018").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/22 15:59
L24	38	((chip die) near3 (top near1 surface)) with waveguide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 16:16
L25	15	((chip die) near3 (top near1 surface)) with (mems (micro near2 sensor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 16:19
L26	21	((chip die) near4 (top near1 surface)) with (mems (micro near2 sensor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 16:45
L27	6	26 not 25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 16:20
L28	13	("5014419"   "5380681"   "5432999"   "5770476"   "5869891"   "5880024"   "5908304"   "5963795"   "5973392"   "6002177"   "6020629"   "6137163"   "6188127").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/22 16:21

## EAST Search History

L29	0	28 and (mems (micro near2 sensor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 16:22
L30	61	((chip die) with (top near1 surface)) with (mems (micro near2 sensor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 16:23
L31	40	30 not 25 not 26 not 27	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 16:24
L32	26403	(forming fabricating) with (mems (micro near2 sensor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 16:47
L33	700	32 and @ay<"2001"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 16:48
L34	4759	(forming fabricating) near3 (mems (micro near2 sensor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 16:48
L35	311	34 and @ay<"2001"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 16:50
L36	210	35 and (wafer die chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 16:50

## EAST Search History

L37	127	35 and (die chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 16:51
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